

YJ Planar Schottky Barrier Diode Die Specification

200V 5A, 65mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB065H200SS-280A

Main Products Characterstics

Maximum Ratings			Static Electrical Characteristics (Ta = 25°C)			
					Value	
					Spec	Typical
					210 V	230V
(tp = 8.3 ms, halfwave, 1 cycle)	I _{FSM}	120 A	Maximum forward voltage drop			
			I _F = 5 A	V _F	0.87V	0.83V
Storage temperature re			≤ 2%			
Maximum operating junction temperature	T _j	175 °C			5uA	0.2uA

Device Schematics and Outline Drawing

Die Thickness *	11 Mils
Die Size **	
Top Metal Pad	60.6 Mils
Active Area	57 Mils
Top Metal	Ag
Back Metal	
Note: 1 * : Also can offer device with 8 mils thickness	
2 **: Cutting street width is around 1.5 mils	

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.	Recommended Storage Environment:
YangjieElectronics does not guarantee device performance after assembly. All operating parameters must be validated for each customer application by customer's technical experts.	Store in original container, in dessicated nitrogen, with no contamination.
Data sheet information is subjected to change without notice.	Shelf life for parts stored in above condition is 2 years.
	If the storage is done in normal atmosphere shelf life is reduced to 6 months.